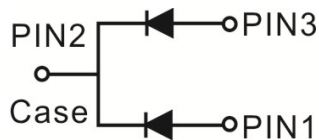
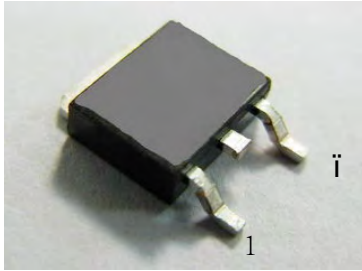


Trench MOS Barrier Schottky Rectifier

763 9



Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

Applications

- DC/DC Converters
- AC/DC Adaptors
- Switching Power Supplies
- Freewheeling Diodes

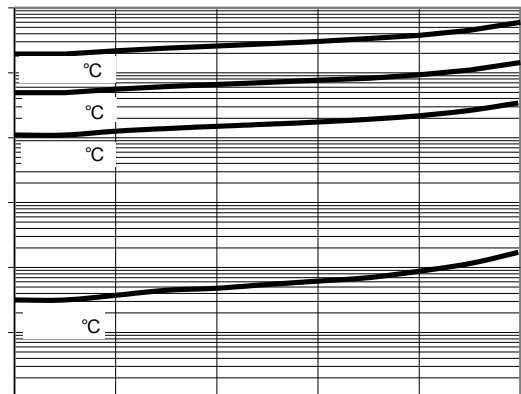
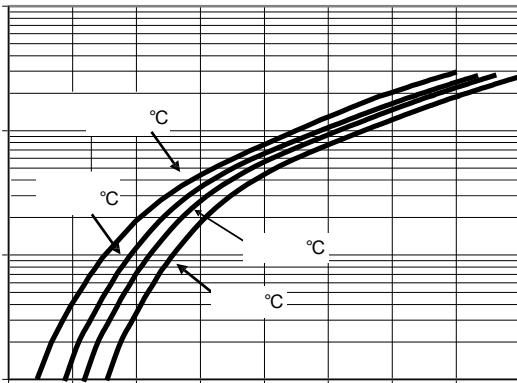
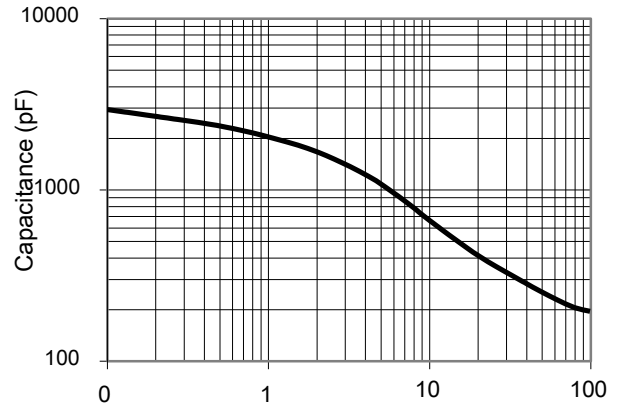
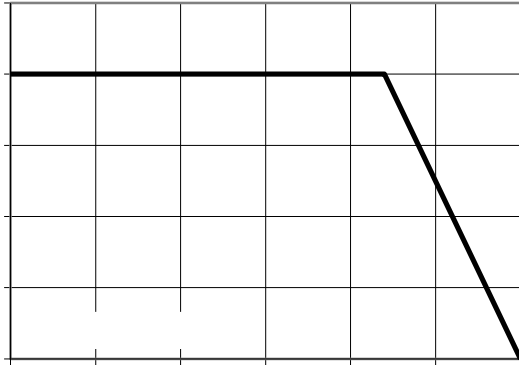
Maximum ratings and electrical characteristics (T_J = 25°C unless otherwise noted)

Parameter		Symbol	Limit		Unit
Maximum repetitive peak reverse voltage		VRRM			V
Maximum average forward rectified current	GHYLFH	IF(AV)			A
	SHUGLRGH				
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode		IFSM			A
Operating junction and storage temperature range		TJ, TSTG	- to +150		°C
Typical thermal resistance per leg	7.2	5 \$ - \$			°C/W
Instantaneous forward voltage per diode			TYP.	MAX.	V
	IF= A	TJ=25°C	0.		
	IF= A	TJ=125°C	0.	-	
	IF= A	TJ=25°C			
Instantaneous reverse current per diode at rated reverse voltage	TJ=25°C	IR(2)	0		uA
	TJ=125°C				mA

Notes:

3XOVH WHVW 3XOVH ZLGWK GXW\F\FOH
 3XOVH WHVW 3XOPWH ZLGWK 0

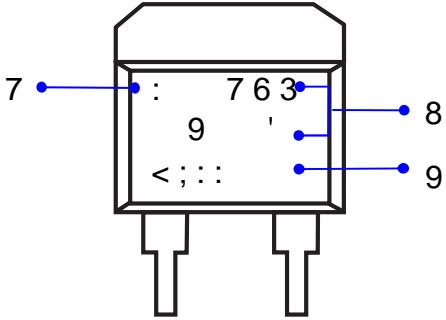
RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)



PACKAGE OUTLINE DIMENSIONS

Note:unit In(mm)

0DUNLQJ ,QIRUPDWLRQ

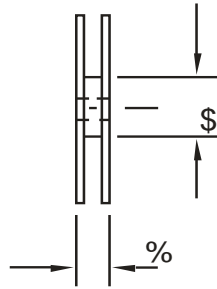
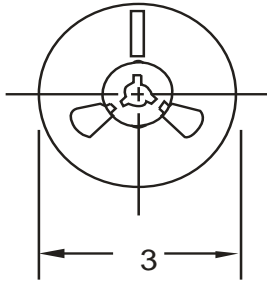


7: &RPSDQ\ V WUDGHPDUN
83URGXFW PRGHO 763 9 '
93' & LQIRUPDWLRQ
< ; ::

:: :HHN FRGH WR
; ,QWHUQDO LGHQWLILFDWLRQ
< <HDU FRGH H[

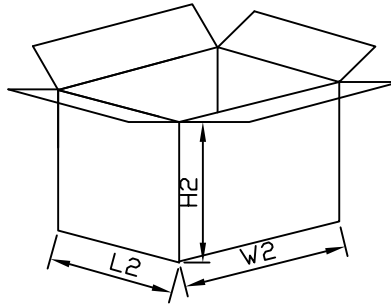
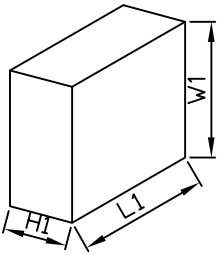
3DFNDJLQJ ,QIRUPDWLRQ

5HHO 'LPHQVLRQV



,QVLGH %R[

2XWVLGH %R[



3DFNDJLQJ ,QIRUPDWLRQ

12	81,7	5HHO 'LPHQVLRQV			,QVLGH %R[2XWVLGH %R[
		&	\$	%	/	:	+	/	:	+
6L]H	PP									
47<	3&6	6PDOO&6UHFWDJH			3&6UHHO&6UHHO&6UHFWDJH			3&6FDUVERQO&6UHFWDJH		
1RWH		7ROHUDQFHPP"PP			PP"PP			PP"PP		